

# Silicon Power Schottky Diode

 $V_{RRM} = 20\text{ V} - 100\text{ V}$ 
 $I_F = 200\text{ A}$ 

## Features

- High Surge Capability
- Types up to 100 V  $V_{RRM}$
- Isolation Type Package

Three Tower Package



Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030 (R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		20	30	35	40	V
RMS reverse voltage	$V_{RMS}$		14	21	25	28	V
DC blocking voltage	$V_{DC}$		20	30	35	40	V
Continuous forward current	$I_F$	$T_C \leq 125\text{ °C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	1500	1500	1500	1500	A
Operating temperature	$T_j$		-40 to 150	-40 to 150	-40 to 150	-40 to 150	°C
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030(R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 100\text{ A}$ , $T_j = 25\text{ °C}$	0.75	0.75	0.75	0.75	V
Reverse current	$I_R$	$V_R = 20\text{ V}$ , $T_j = 25\text{ °C}$	1	1	1	1	mA
		$V_R = 20\text{ V}$ , $T_j = 125\text{ °C}$	20	20	20	20	

## Thermal characteristics

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030 (R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Thermal resistance, junction - case	$R_{thJC}$		0.18	0.18	0.18	0.18	°C/W

Figure .1- Typical Forward Characteristics

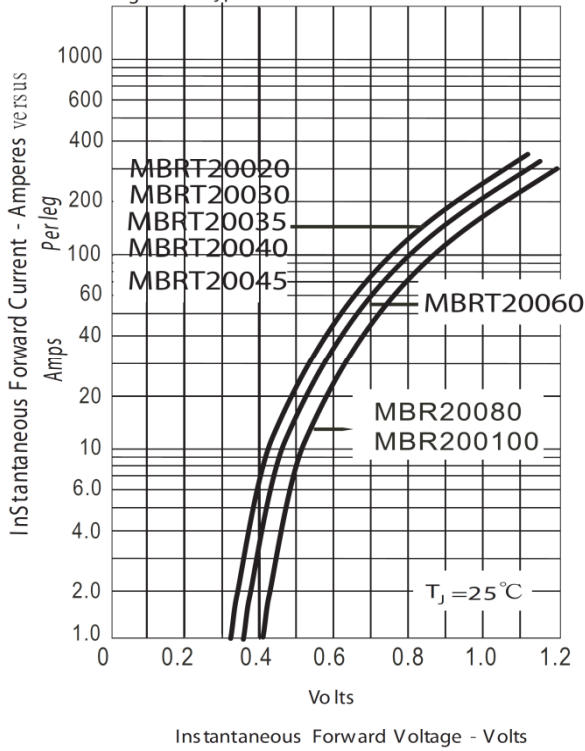


Figure .2- Forward Derating Curve

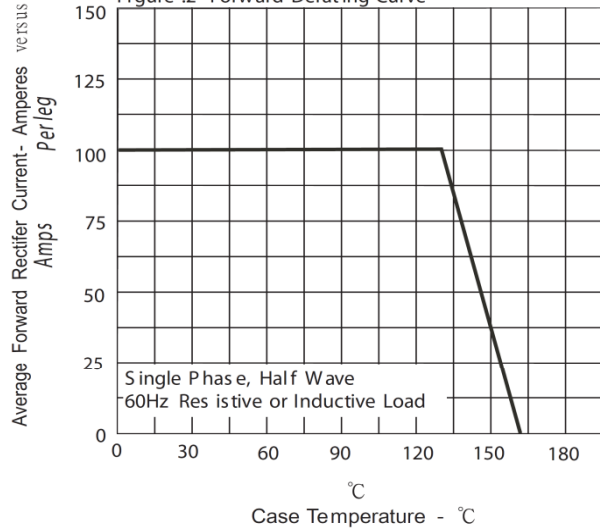


Figure.3-Peak Forward Surge Current

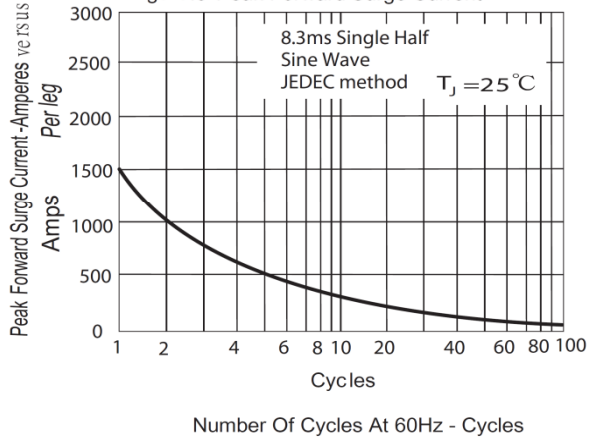


Figure .4- Typical Reverse Characteristics

